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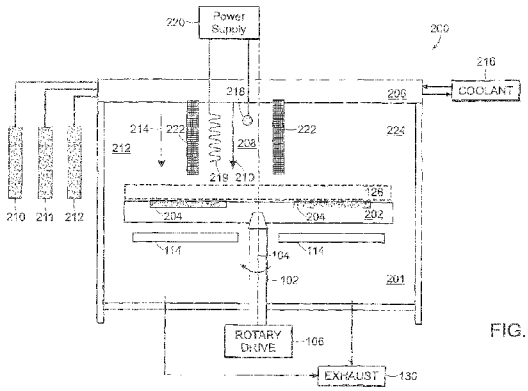


FIG. 2

(57) **Abstract**: A vapor phase epitaxy system includes a platen that supports substrates for vapor phase epitaxy and a gas injector. The gas injector injects a first precursor gas into a first region and injects a second precursor gas into a second region. At least one electrode is positioned in the first region so that first precursor gas molecules flow proximate to the electrode. The at least one electrode is positioned to be substantially isolated from a flow of the second precursor gas. A power supply is electrically connected to the at least one electrode. The power supply generates a current that heats the at least one electrode so as to thermally activate at least some of the first precursor gas molecules flowing proximate to the at least one electrode, thereby activating first precursor gas molecules.

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